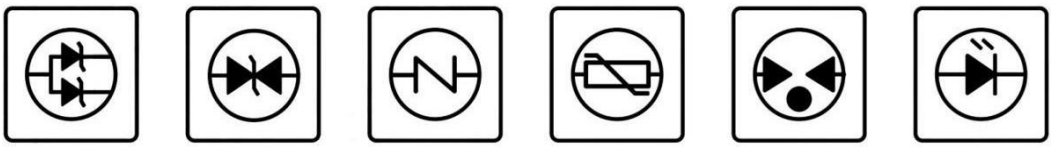
MSKSEMI 美森科
SEMICONDUCTOR



RS2MF

Product specification

VOLTAGE RANGE 50 to 1000 Volts CURRENT 2.0 Ampere

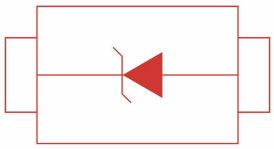
Features

- Ideal for surface mount applications
- Easy pick and place
- Built-in strain relief
- Fast switching speed

MECHANICAL DATA

- Case: Molded plastic
- Epoxy: UL 94V-0 rate flame retardant
- Metallurgically bonded construction
- Polarity: Color band denotes cathode end
- Mounting position: Any

Reference News

PACKAGE OUTLINE	PINConfiguratio	Marking
		RS2MF
SMAF		

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25 ˚C ambient temperature uniess otherwies specified.
Single phase half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

P/N(MARK)		RS2AF	RS2BF	RS2DF	RS2GF	RS2JF	RS2KF	RS2MF	UNITS
Maximum Recurrent Peak Reverse Voltage		50	100	200	400	600	800	1000	V
Maximum RMS Voltage		35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage		50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at Ta=90℃		2.0							A
Peak Forward Surge Current, 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)		50							A
Maximum Instantaneous Forward Voltage at 2.0A		1.3							V
Maximum DC Reverse Current at Rated DC Blocking Voltage	Ta=25℃	5.0							μA
	Ta=100℃	150							μA
Maximum Reverse Recovery Time (Note 1)		150				250	500		nS
Typical Junction Capacitance (Note 2)		50							pF
Operating and Storage Temperature Range T_J, T_{STG}		-65——+150							℃

NOTES:

1. Reverse Recovery Time test condition: IF=0.5A, IR=1.0A, IRR=0.25A
2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

RATING AND CHARACTERISTIC CURVES (RS2AF THRU RS2MF)

FIG.1-TYPICAL FORWARD CHARACTERISTICS

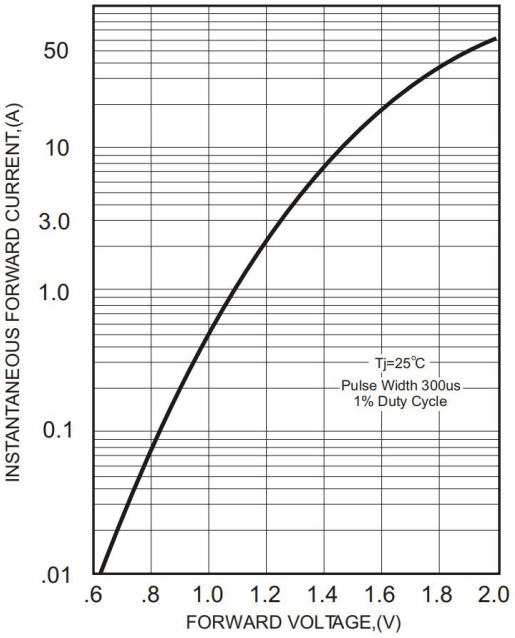


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

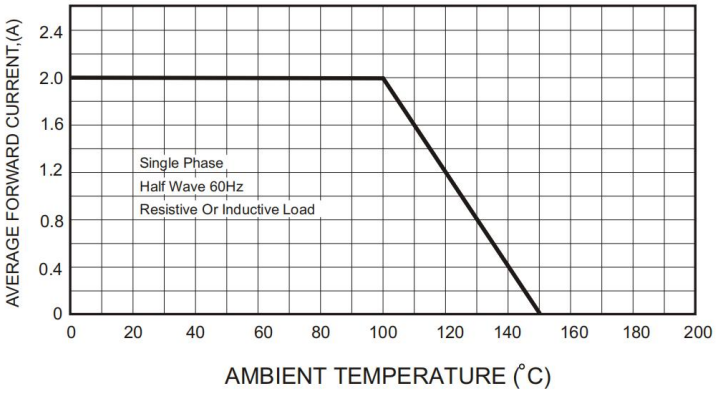
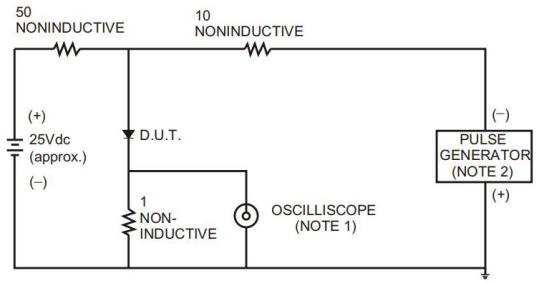
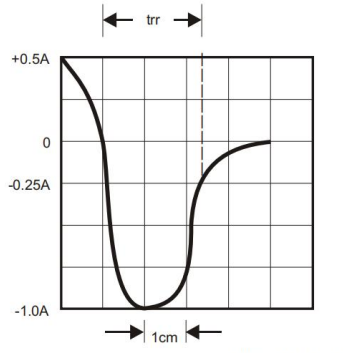


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm.22pF.

2. Rise Time= 10ns max., Source Impedance= 50 ohms.



SET TIME BASE FOR
50 / 10ns / cm

FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

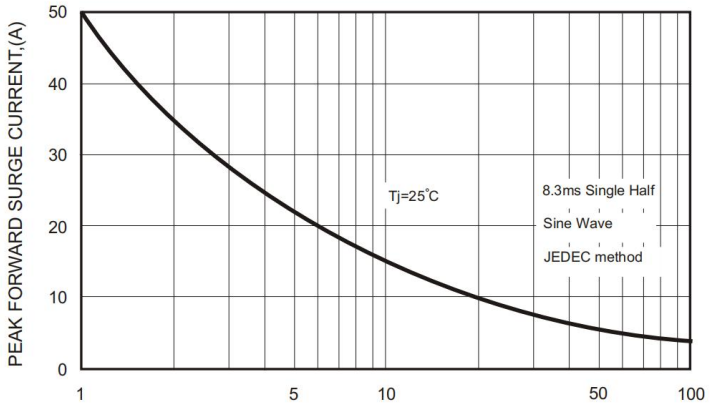
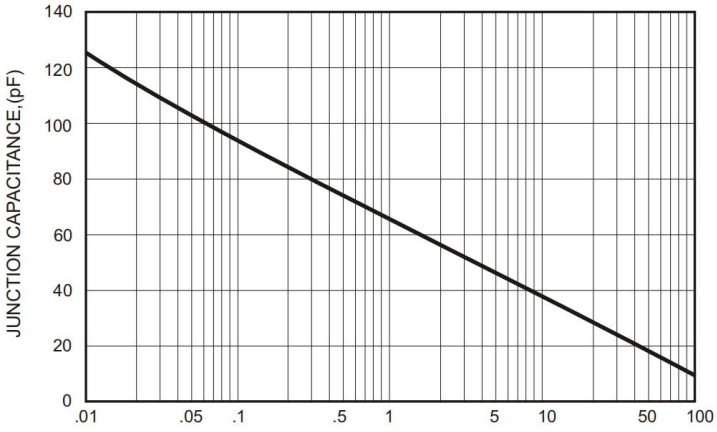
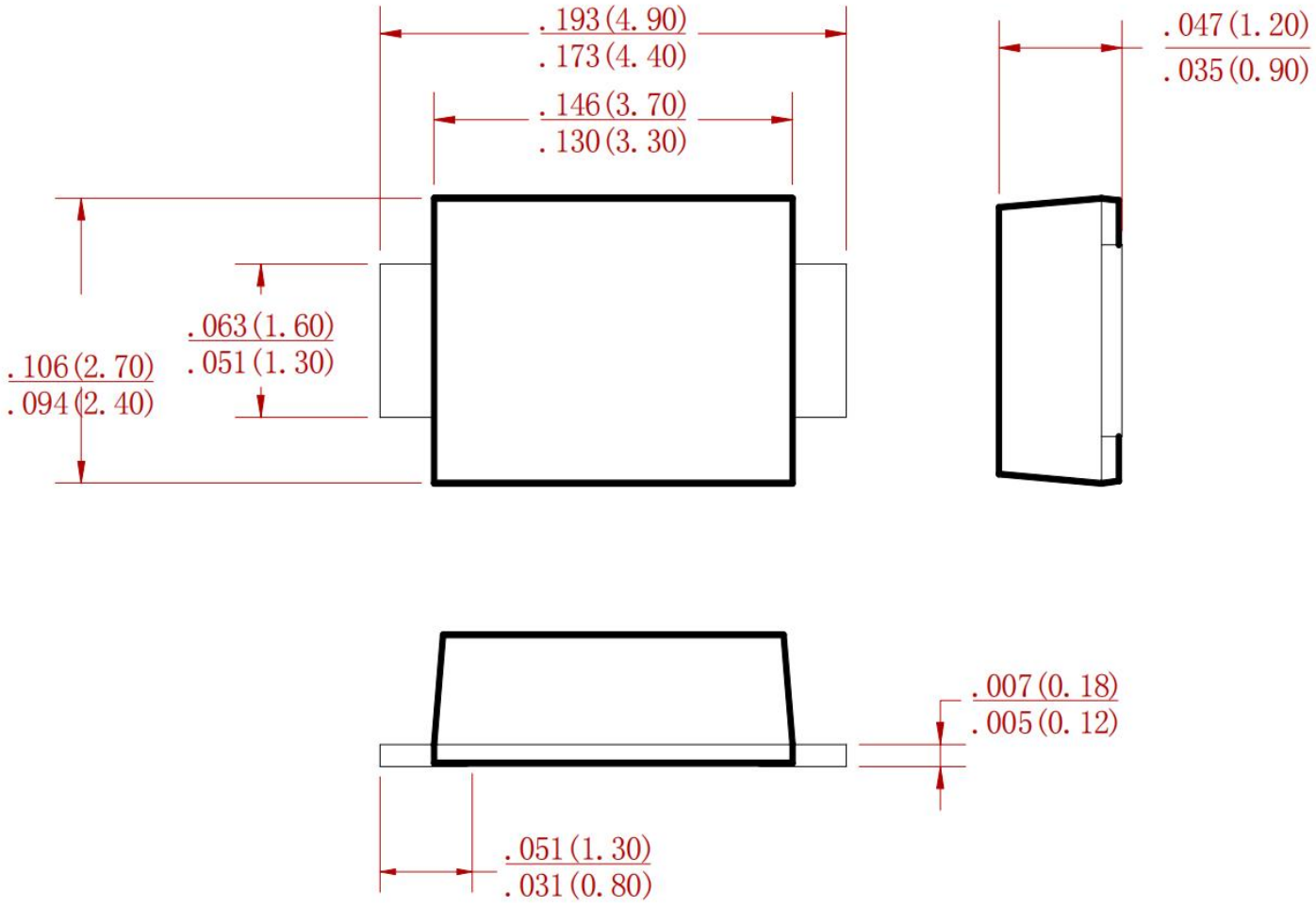


FIG.5-TYPICAL JUNCTION CAPACITANCE



PACKAGE MECHANICAL DATA



Dimensions in inches and (millimeters)

REEL SPECIFICATION

P/N	PKG	QTY
RS2AF THRU RS2MF	SMAF	3000

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